

LED CHIP C890-40P

SPECIFICATION OF LED CHIP
C890-40P
[INFRARED]

1) Commodity Type and Physical Characteristics.

- 1. Material GaAlAs
- 2. Electrode Top Side N (cathode)side :Au Alloy & Pad
Bottom Side P (anode)side :Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.33	1.45	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.5	3.5		mW
Peak Wavelength	λ P	If=20mA	880	890	900	nm
Spectral Radiation Bandwidth	DI	If=20mA		80		nm
Rise Time	tr	If=20mA		500		ns
Full time	tf	If=20mA		1000		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

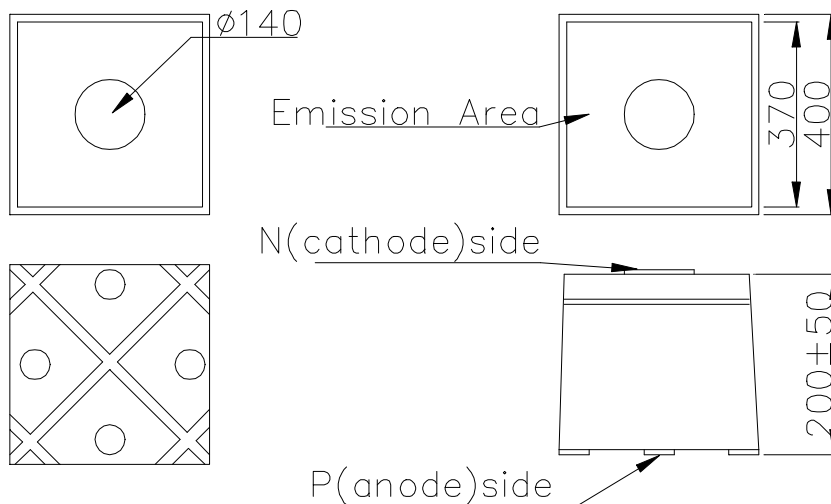


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area